MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED







Description

The MSRV05-4 is designed to protect voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium.

Features

- IEC 61000-4-2 Level 4 ESD Protection
 - ±12kV Contact Discharge
 - ±17kV Air Discharge
- 60W Peak pulse Power (8/20us)
- Low clamping voltage
- Working voltage: 5V
- Low leakage current
- RoHS compliant
- Protecting 4 unidirectional lines
- Ultra-low capacitance: 0.6pF Typ.

Applications

- USB 2.0
- Monitors and flat panel displays
- 10/100/1000 ethernet
- Notebook computers
- SIM ports
- ATM interface

Reference News

Outline	Circuit Diagram	Marking
50T-23-6		.V05

Pin Configuration and Functions

Pin	Name	Description	Pin	Name	Description
1	IO1	Connect to I/O	4	IO3	Connect to I/O
2	GND	Connect to GND	5	Vcc	Connect to Vcc
3	IO2	Connect to I/O	6	104	Connect to I/O



Absolute Maximum rating

Over operating free-air temperature range (unless otherwise noted)

Parameters	Symbol	Min.	Max.	Unit
Peak pulse power (tp=8/20us)@25°C	P _{pk}	-	60	W
Peak pulse current (tp=8/20us)@25°C	I _{PP}		4.5	А
ESD (IEC61000-4-2 air discharge) @25°C	Vesd	-	±17	kV
ESD (IEC61000-4-2 contact discharge) @25°C	Vesd	-	±12	kV
Junction temperature	TJ	-	150	°C
Operating temperature	Top	-40	125	°C
Storage temperature	Tstg	-55	150	°C
Lead temperature	T∟	-	260	°C

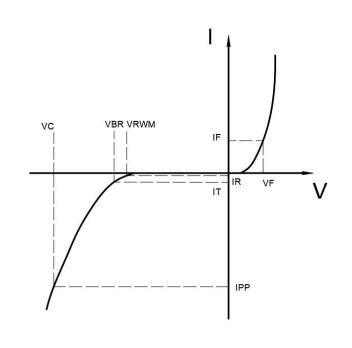
Electrical Characteristics

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Reverse Stand-off Voltage	V _{RWM}				5	V
Reverse Breakdown Voltage	V_{BR}	IT=1mA	6			V
Reverse Leakage Current	I _R	V _{RWM} =5V			1	uA
Clamping Voltage	Vc	I _{PP} =1A; tp=8/20us		9		V
Clamping Voltage	Vc	I _{PP} =4.5A; tp=8/20us		12		V
Junction Capacitance	CJ	I/O to GND; VR=0V; f=1MHz		0.6	0.8	pF
	C,	Between I/O; VR=0V; f=1MHz		0.3	0.4	pF

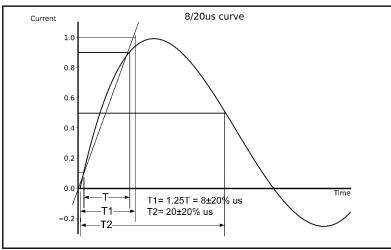
MSKSEMI SEMICONDUCTOR

MSRV05-4

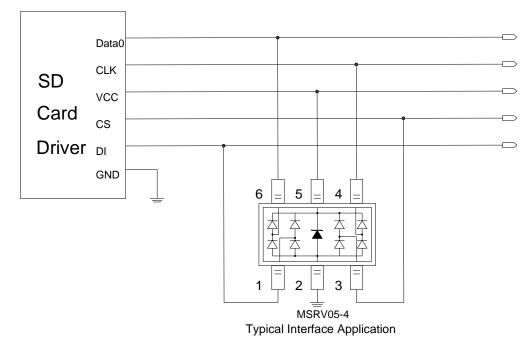
Symbol	Parameters
V _{RWM}	Peak Reverse Working Voltage
IR	Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I⊤
ҥ	Test Current
I _{PP}	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @ IPP
F	Forward Current
VF	Forward Voltage @ I _F



Typical Characteristic



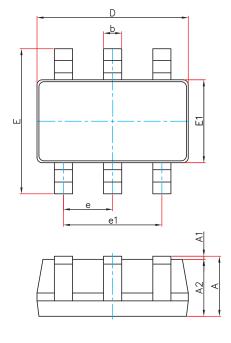
Typical Application

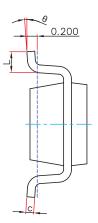


.



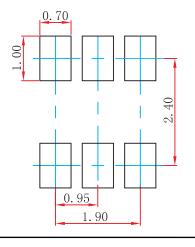
SOT-23-6 Package Outline Dimensions





Symbol	Dimensions In	n Millimeters	Dimension	s In Inches
Symbol	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
е	0.950(BSC)		0.037	(BSC)
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°
θ				

SOT-23-6 Suggested Pad Layout



Note:

1.Controlling dimension: in millimeters. 2.General tolerance:± 0.05mm.

3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MSRV05-4	SOT-23-6	3000



Attention

■ Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.

MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all MSKSEMI Semiconductor products described or contained herein.

Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuits for safedesign, redundant design, and structural design.

■ In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or

mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.

Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements intellectual property rights or other rights of third parties.

Any and all information described or contained herein are subject to change without notice due to

product/technology improvement, etc. Whendesigning equipment, referto the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.